

Product data sheet

1. General description

Hyperfast power diode in a SOT429 (3-lead TO247) plastic package.

2. Features and benefits

- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 115 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	30	A
Static chara	cteristics						
V _F	forward voltage	I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.38	1.8	V
Dynamic ch	aracteristics	·	1				
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	18	22	ns





5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode		K – K – A
2	К	cathode		001aaa020
3	А	anode		
mb	mb	mounting base; connected to cathode	TO-247 (SOT429)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BYC30WT-600P	TO-247	plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3 lead TO-247	SOT429				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BYC30WT-600P	BYC30WT-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 115 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	30	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 115 °C; square-wave pulse	-	60	А

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Symbol	Parameter	Conditions	IV	lin	Max	Unit
	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-		270	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-		300	A
T _{stg}	storage temperature		-1	65	175	°C
Tj	junction temperature		-		175	°C

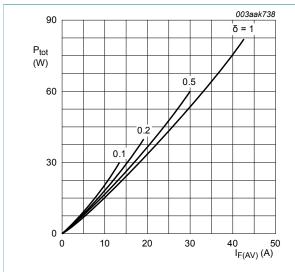
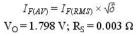
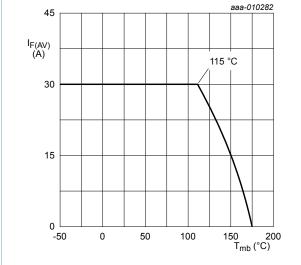
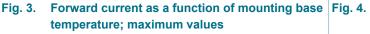


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values







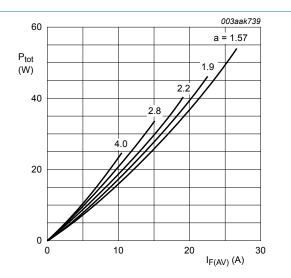
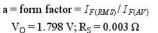
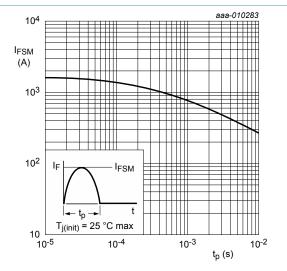


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



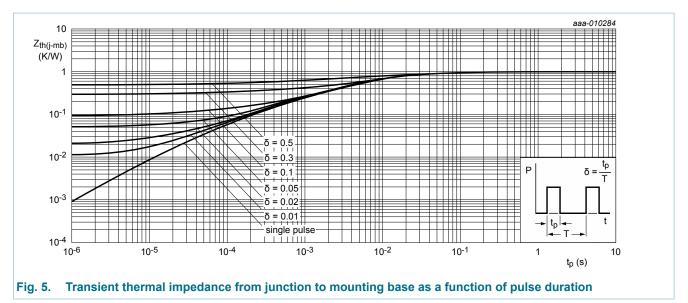


4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	45	-	K/W



10. Characteristics

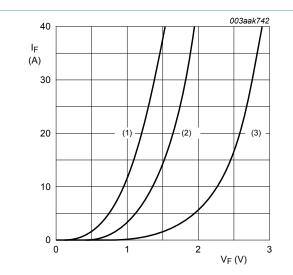
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		·			
V _F forward voltage		I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.38	1.8	V
I _R reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA	
		V _R = 600 V; T _j = 150 °C	-	-	1	mA
Dynamic cl	naracteristics		I			
Q _r recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; T _j = 25 °C; <u>Fig. 7</u>	-	50	-	nC	
		I_F = 30 A; V_R = 200 V; dI_F/dt = 200 A/ µs; T_j = 125 °C; <u>Fig. 7</u>	-	280	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 200 A/µs; T _j = 25 °C; <u>Fig. 7</u>	-	18	22	ns
		I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	35	-	ns
		I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 125 °C; <u>Fig. 7</u>	-	70	-	ns
		I _F = 30 A; V _R = 400 V; dI _F /dt = 500 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	29	-	ns
I _{RM}	peak reverse recovery current	I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	3.5	-	A
		I_F = 30 A; V _R = 200 V; dI _F /dt = 200 A/ µs; T _j = 125 °C; <u>Fig. 7</u>	-	7.6	-	A





 (1) T_j = 150 °C; typical values;
(2) T_j = 150 °C; maximum values;
(3) T_j = 25 °C; maximum values; V_O = 1.798 V; R_S = 0.003 Ω

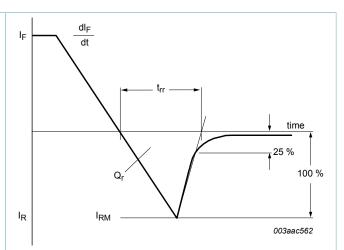
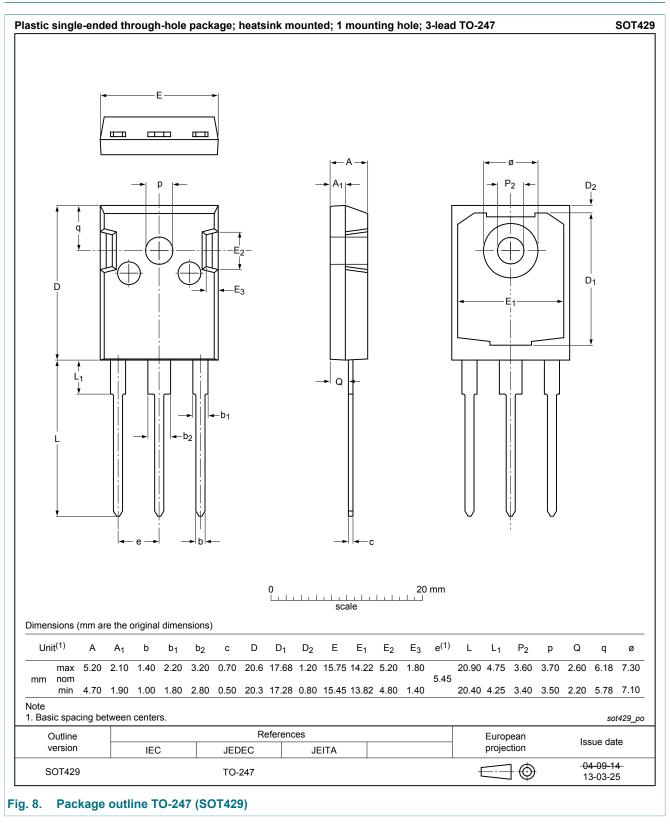


Fig. 7. Reverse recovery definitions; ramp recovery



11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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